

SiMS measurements & Simulation, Varied bias rail geometry structures characterization and TCAD simulation

Thursday 12 June 2014 09:00 (20 minutes)

Secondary Ion Mass Spectroscopy measurements, conducted to calibrate the new edgeless pixel production for the High Luminosity upgrade of the LHC, are being compared with TCAD simulated doping profiles for n and p implanted wafers. On the same context, simulation and characterization of varied bias rail geometry structures is being presented in an attempt to understand and compensate for the efficiency drop issue under the biasing gird region. Through 3D profile and field simulation, the structures under investigation are being compared with experimental measurements.

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Session Classification: Session 3 - TCAD simulations